

Specification	Products	SST / SOT-23	Type	BC807	BC807
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FD:514-807

1. SCOPE BC807

1.1 Scope. This specification covers the detail requirements for one type PNP silicon epitaxial planar transistor designed for audio frequency small signal amplifier.

1.2 Physical dimensions. See figure 1.

1.3 Absolute maximum ratings. (T_a = 25°C)

Collector to base voltage	V _{CBO}	- 50 V
Collector to emitter voltage	V _{CEO}	- 45 V
Emitter to base voltage	V _{EBO}	- 5 V
Collector current	I _C	- 800 mA
Power dissipation-Free Air	P _C	200 mW
* Power dissipation-Ceramic Substrate	P _C	330 mW
Junction temperature	T _j	150°C
Storage temperature range	T _{stg}	- 55 ~ 150°C

* Package mounted on ceramic 7×5×0.6mm

2. Electrical characteristics (T_a = 25°C)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV _{CBO}	I _C = -100 μA	-50	-	-	V
BV _{CEO}	I _C = -10 mA	-45	-	-	V
BV _{EBO}	I _E = -10 μA	-5	-	-	V
IC _{BO}	V _{CB} = -25 V	-	-	-100	nA
IE _{BO}	V _{EB} = -4 V	-	-	-100	nA
V _{CE(sat)}	I _C = -500 mA, I _B = -50 mA	-	-	-0.7	V
V _{BE(sat)}	I _C = -500 mA, I _B = -50 mA	-	-	-2.0	V
hFE 1	V _{CE} = -1 V, I _C = -100 mA	100	-	400	-
hFE 2	V _{CE} = -1 V, I _C = -300 mA	60	-	-	-
f _T	V _{CB} = -5 V, I _E = -50 mA, f = 20 MHz	-	150	-	MHz
C _{ob}	V _{CB} = -10 V, f = 1 MHz	-	10	-	pF
C _{ib}	V _{EB} = -0.5 V, f = 1 MHz	-	60	-	pF
IC _{BO}	V _{CB} = -25 V, T _a = 150°C	-	-	-5	μA

This parts are classified into the categories below and given hFE item.

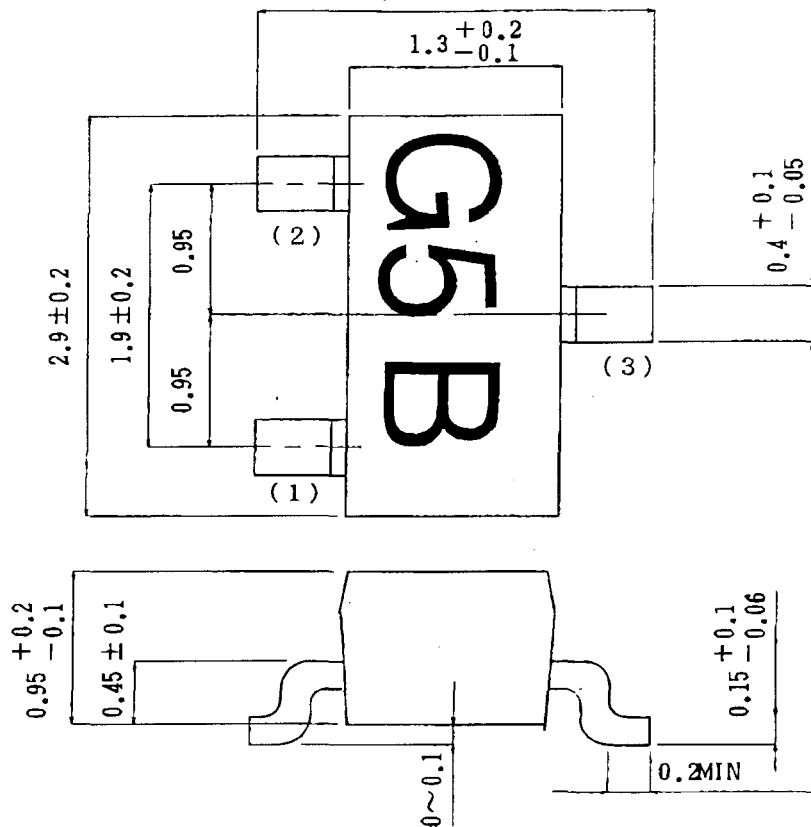
Part No.	BC807-16	BC807-25
hFE 1	100~250	160~400
hFE 2	60~	100~

Specification	Products	SST	Type	BC807
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DIMENSION

2.4±0.2

FD:fig-8227



- (1) Emitter
- (2) Base
- (3) Collector

UNIT : mm

The net weight
9 mg / p c e

'G 5' is symbol mark of BC 8 0 7. Marking Code BC807-16 . . . G 5 A
BC807-25 . . . G 5 B

* Two kinds of marking.

'3 5' means the production week.
Its direction signifies odd year, or even year.
ODD YEAR (ex:35th) EVEN YEAR (ex:35th)

